University Menoufia

Faculty Electronic Engineering

: Electronics Department and

Communications

Engineering

Academic level : First Year Course Name : Electronics (2)

Course Code : ECE 123



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No. of pages:

Full Mark: 35 Marks Exam : Final Exam : Assoc. Prof. Examiner

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Question 1. Complete the following	sentences with	the correct answer: (15	Marks)
i) JFET is abbreviation to, whil	e MOSFET is ab	breviation to	
ii) A major advantages of FET trans	istors are		
iii) A FET is aco	ontrolled device).	
iv) The basic terminals of FET trans	istors are	,, and	
v) The main difference between d	epletion mode	and enhancement mode	in FET
transistor is			
vi) V_P in FET transistor is called by	w1	here the basic types of bia	asing in
FET transistor are		and	
vii) Forward transconductance (gm)	is rate of chan	ge ofto	the rate
of change of	.when	is cons	tant.

Question 2.

(20 Marks)

- a) The 2N5459 JFET has typically I_{DSS} =9 mA, $V_{GS(OFF)}$ =-8 V (maximum). Using these values, determine the drain current for $V_{GS}=0$ V, -1 V, and -4 V.
- b) Voltage divider N channel enhancement MOSFET common source amplifier. Sketch the basic amplifier circuit diagram, sketch the small signal equivalent circuit and then find overall voltage gain. Sketch the output waveform for this circuit.
- c) IFET with voltage divider bias circuit has the following parameters: V_{DD}=12 V, R_D =3.3 K Ω , R_S =2.2 K Ω , R_1 =6.8 M Ω , R_2 =1 M Ω , and V_D =7 V. Sketch the schematic view of the circuit. Estimate the gate voltage, the drain current, gate to source voltage and drain to source voltage.

مع تمنياتي لكم بالنجاج والتوفيق